



National Semiconductor

January 1988

# **MM54HC00/MM74HC00**

## **Quad 2-Input NAND Gate**

## **General Description**

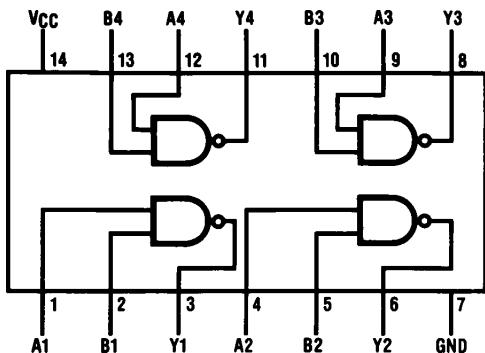
These NAND gates utilize advanced silicon-gate CMOS technology to achieve operating speeds similar to LS-TTL gates with the low power consumption of standard CMOS integrated circuits. All gates have buffered outputs. All devices have high noise immunity and the ability to drive 10 LS-TTL loads. The 54HC/74HC logic family is functionally as well as pin-out compatible with the standard 54LS/74LS logic family. All inputs are protected from damage due to static discharge by internal diode clamps to V<sub>CC</sub> and ground.

## Features

- Typical propagation delay: 8 ns
  - Wide power supply range: 2–6V
  - Low quiescent current: 20  $\mu$ A maximum (74HC Series)
  - Low input current: 1  $\mu$ A maximum
  - Fanout of 10 LS-TTL loads

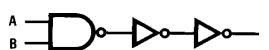
## Connection and Logic Diagrams

## Dual-In-Line Package



TL/F/5292-1

Order Number MM54UC00 or MM74UC00



TL/F/5292-2

## Absolute Maximum Ratings (Notes 1 & 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

Supply Voltage ( $V_{CC}$ )	−0.5 to +7.0V
DC Input Voltage ( $V_{IN}$ )	−1.5 to $V_{CC} + 1.5V$
DC Output Voltage ( $V_{OUT}$ )	−0.5 to $V_{CC} + 0.5V$
Clamp Diode Current ( $I_{IK}, I_{OK}$ )	±20 mA
DC Output Current, per pin ( $I_{OUT}$ )	±25 mA
DC $V_{CC}$ or GND Current, per pin ( $I_{CC}$ )	±50 mA
Storage Temperature Range ( $T_{STG}$ )	−65°C to +150°C

Power Dissipation ( $P_D$ )

(Note 3)	600 mW
S.O. Package only	500 mW

Lead Temperature ( $T_L$ )

(Soldering 10 seconds)	260°C
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## DC Electrical Characteristics (Note 4)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ		$T_A = -40 \text{ to } 85^\circ C$	$T_A = -55 \text{ to } 125^\circ C$	
$V_{IH}$	Minimum High Level Input Voltage		2.0V 4.5V 6.0V	1.5 3.15 4.2		1.5 3.15 4.2	1.5 3.15 4.2	V
$V_{IL}$	Maximum Low Level Input Voltage**		2.0V 4.5V 6.0V	0.5 1.35 1.8		0.5 1.35 1.8	0.5 1.35 1.8	V
$V_{OH}$	Minimum High Level Output Voltage	$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 20 \mu A$	2.0V 4.5V 6.0V	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{IN} = V_{IH}$ or $V_{IL}$ $ I_{OUT}  \leq 4.0 \text{ mA}$ $ I_{OUT}  \leq 5.2 \text{ mA}$	4.5V 6.0V	4.2 5.7	3.98 5.48	3.84 5.34	3.7 5.2	V
$V_{OL}$	Maximum Low Level Output Voltage	$V_{IN} = V_{IH}$ $ I_{OUT}  \leq 20 \mu A$	2.0V 4.5V 6.0V	0 0 0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{IN} = V_{IH}$ $ I_{OUT}  \leq 4.0 \text{ mA}$ $ I_{OUT}  \leq 5.2 \text{ mA}$	4.5V 6.0V	0.2 0.2	0.26 0.26	0.33 0.33	0.4 0.4	V
$I_{IN}$	Maximum Input Current	$V_{IN} = V_{CC}$ or GND	6.0V		±0.1	±1.0	±1.0	$\mu A$
$I_{CC}$	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$	6.0V		2.0	20	40	$\mu A$

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: −12 mW/°C from 65°C to 85°C; ceramic "J" package: −12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V ±10% the worst case output voltages ( $V_{OH}$  and  $V_{OL}$ ) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case  $V_{IH}$  and  $V_{IL}$  occur at  $V_{CC} = 5.5V$  and 4.5V respectively. (The  $V_{IH}$  value at 5.5V is 3.85V.) The worst case leakage current ( $I_{IN}$ ,  $I_{CC}$ , and  $I_{OZ}$ ) occur for CMOS at the higher voltage and so the 6.0V values should be used.

\*\* $V_{IL}$  limits are currently tested at 20% of  $V_{CC}$ . The above  $V_{IL}$  specification (30% of  $V_{CC}$ ) will be implemented no later than Q1, CY'89.

## Operating Conditions

	Min	Max	Units
Supply Voltage ( $V_{CC}$ )	2	6	V
DC Input or Output Voltage ( $V_{IN}, V_{OUT}$ )	0	$V_{CC}$	V
Operating Temp. Range ( $T_A$ )			
MM74HC	−40	+85	°C
MM54HC	−55	+125	°C
Input Rise or Fall Times ( $t_r, t_f$ )			
$V_{CC} = 2V$	1000	ns	
$V_{CC} = 4.5V$	500	ns	
$V_{CC} = 6.0V$	400	ns	

**AC Electrical Characteristics**  $V_{CC} = 5V$ ,  $T_A = 25^\circ C$ ,  $C_L = 15 \text{ pF}$ ,  $t_r = t_f = 6 \text{ ns}$

Symbol	Parameter	Conditions	Typ	Guaranteed Limit	Units
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay		8	15	ns

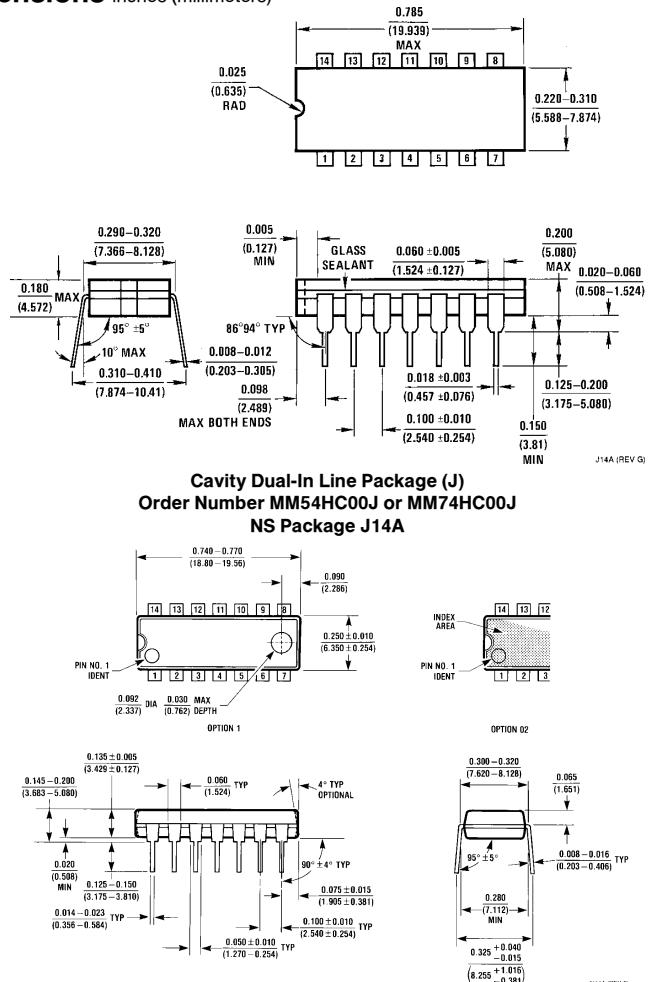
**AC Electrical Characteristics**  $V_{CC} = 2.0V \text{ to } 6.0V$ ,  $C_L = 50 \text{ pF}$ ,  $t_r = t_f = 6 \text{ ns}$  (unless otherwise specified)

Symbol	Parameter	Conditions	$V_{CC}$	$T_A = 25^\circ C$		$74HC$	$54HC$	Units
				Typ	Guaranteed Limits			
$t_{PHL}, t_{PLH}$	Maximum Propagation Delay		2.0V 4.5V 6.0V	45 9 8	90 18 15	113 23 19	134 27 23	ns ns ns
$t_{TLH}, t_{THL}$	Maximum Output Rise and Fall Time		2.0V 4.5V 6.0V	30 8 7	75 15 13	95 19 16	110 22 19	ns ns ns
$C_{PD}$	Power Dissipation Capacitance (Note 5)	(per gate)		20				pF
$C_{IN}$	Maximum Input Capacitance			5	10	10	10	pF

**Note 5:**  $C_{PD}$  determines the no load dynamic power consumption,  $P_D = C_{PD} V_{CC}^2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .

# MM54HC00/MM74HC00 Quad 2-Input NAND Gate

## Physical Dimensions inches (millimeters)



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